

2SK3030

Silicon N-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON resistance R_{on}
- No secondary breakdown
- Low-voltage drive
- High electrostatic energy capability

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

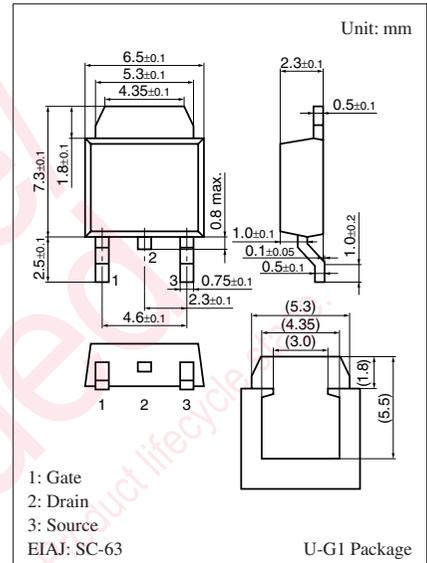
Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	100	V
Gate-source surrender voltage	V_{GSS}	± 20	V
Drain current	I_D	± 8	A
Peak drain current	I_{DP}	± 24	A
Avalanche energy capability *	EAS	3.2	mJ
Power dissipation	P_D	15	W
		1	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: $L = 0.1$ mH, $I_L = 8$ A, 1 pulse

■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

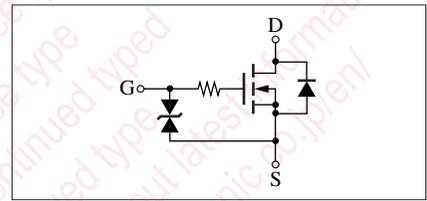
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 1$ mA, $V_{GS} = 0$	100			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 80$ V, $V_{GS} = 0$			10	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 20$ V, $V_{DS} = 0$			± 10	μA
Gate threshold voltage	V_{th}	$V_{DS} = 10$ V, $I_D = 1$ mA	1.0		2.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10$ V, $I_D = 4$ A	2	4		S
Drain-source ON resistance	$R_{DS(on)1}$	$V_{GS} = 10$ V, $I_D = 4$ A		0.15	0.23	Ω
	$R_{DS(on)2}$	$V_{GS} = 4$ V, $I_D = 4$ A		0.18	0.26	
Diode forward voltage	V_{DSF}	$I_{DR} = 8$ A, $V_{GS} = 0$			-1.4	V
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ MHz		290		pF
Short-circuit output capacitance (Common source)	C_{oss}			110		pF
Reverse transfer capacitance (Common source)	C_{rss}			30		pF
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30$ V, $I_D = 4$ A, $R_L = 7.5$ Ω		15		ns
Rise time	t_r	$V_{GS} = 10$ V		40		ns
Fall time	t_f			200		ns
Turn-off delay time	$t_{d(off)}$			860		ns
Thermal resistance (ch-c)	$R_{th(ch-c)}$				8.33	$^\circ\text{C/W}$
Thermal resistance (ch-a)	$R_{th(ch-a)}$				125	$^\circ\text{C/W}$

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



Marking Symbol: K3030

Internal Connection



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